

## UT30N03

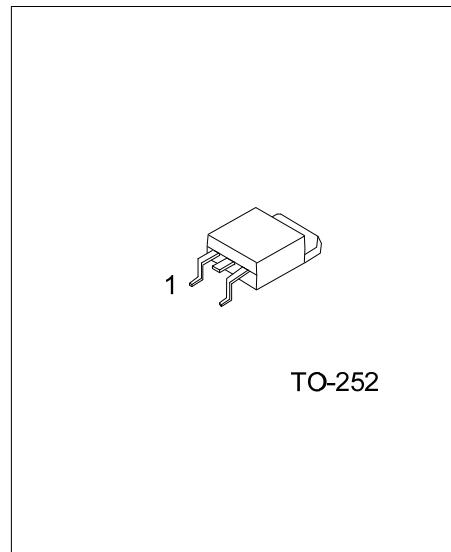
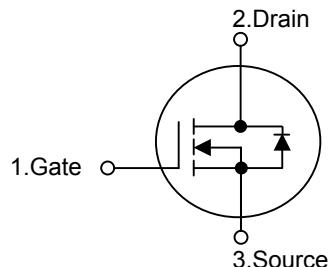
Power MOSFET

N-CHANNEL  
ENHANCEMENT MODE

## ■ FEATURES

- \*  $R_{DS(ON)} = 30m\Omega$  @ $V_{GS} = 10 V$
- \* Low Capacitance
- \* Optimized gate charge
- \* Fast switching capability
- \* Avalanche energy specified

## ■ SYMBOL



\*Pb-free plating product number: UT30N03L

## ■ ORDERING INFORMATION

| Ordering Number |                | Package | Pin Assignment |   |   | Packing   |
|-----------------|----------------|---------|----------------|---|---|-----------|
| Lead Free       | Halogen Free   |         | 1              | 2 | 3 |           |
| UT30N03L-TN3-R  | UT30N03G-TN3-R | TO-252  | G              | D | S | Tape Reel |
| UT30N03L-TN3-T  | UT30N03G-TN3-T | TO-252  | G              | D | S | Tube      |

|                |                 |                                    |
|----------------|-----------------|------------------------------------|
| UT30N03L-TN3-R | (1)Packing Type | (1) R: Tape Reel, T: Tube          |
|                | (2)Package Type | (2) TN3: TO-252                    |
|                | (3)Lead Plating | (3) L: Lead Free , G: Halogen Free |

■ ABSOLUTE MAXIMUM RATINGS ( $T_J=25^\circ\text{C}$ , unless otherwise specified)

| PARAMETER                | SYMBOL    | RATINGS    | UNIT             |
|--------------------------|-----------|------------|------------------|
| Drain-Source Voltage     | $V_{DS}$  | 30         | V                |
| Gate-Source Voltage      | $V_{GS}$  | $\pm 20$   | V                |
| Continuous Drain Current | $I_D$     | 30         | A                |
| Pulsed Drain Current     | $I_{DM}$  | 40         | A                |
| Avalanche Energy         | $E_{AS}$  | 90         | mJ               |
| Power Dissipation        | $P_D$     | 50         | W                |
| Junction Temperature     | $T_J$     | +175       | $^\circ\text{C}$ |
| Storage Temperature      | $T_{STG}$ | -55 ~ +175 | $^\circ\text{C}$ |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied

## ■ THERMAL DATA

| PARAMETER           | SYMBOL        | MIN | TYP | MAX | UNIT                      |
|---------------------|---------------|-----|-----|-----|---------------------------|
| Junction-to-Ambient | $\theta_{JA}$ |     |     | 50  | $^\circ\text{C}/\text{W}$ |
| Junction-to-Case    | $\theta_{JC}$ |     |     | 3.0 | $^\circ\text{C}/\text{W}$ |

■ ELECTRICAL CHARACTERISTICS ( $T_J=25^\circ\text{C}$ , unless otherwise specified)

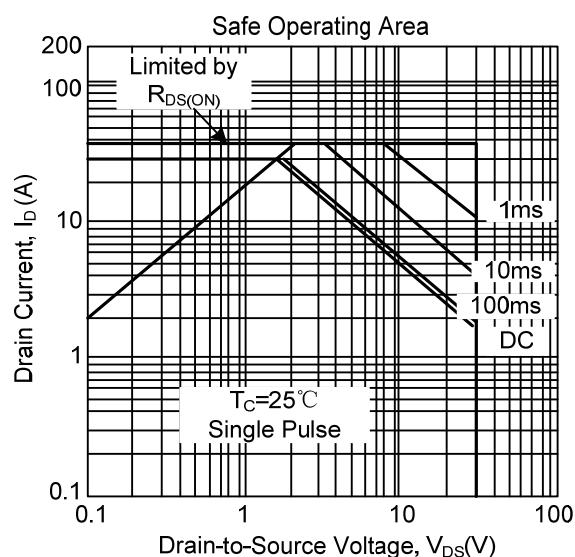
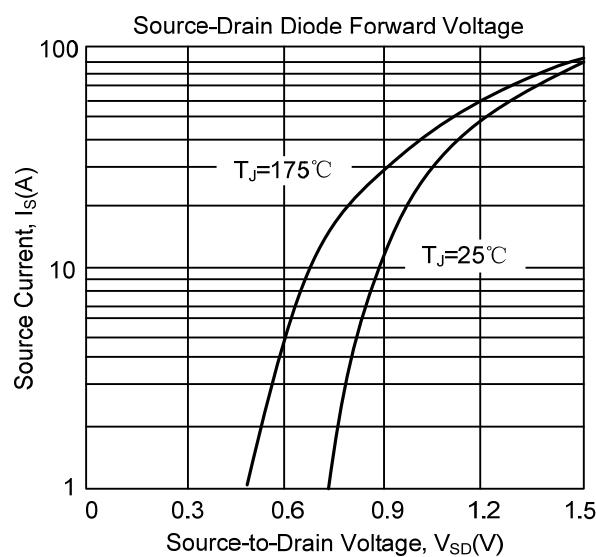
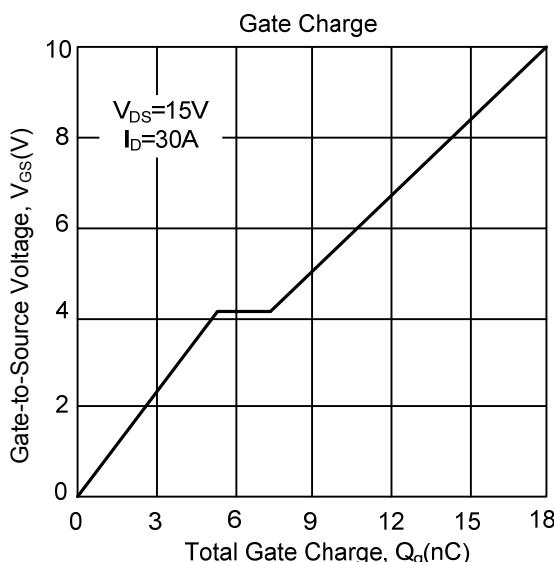
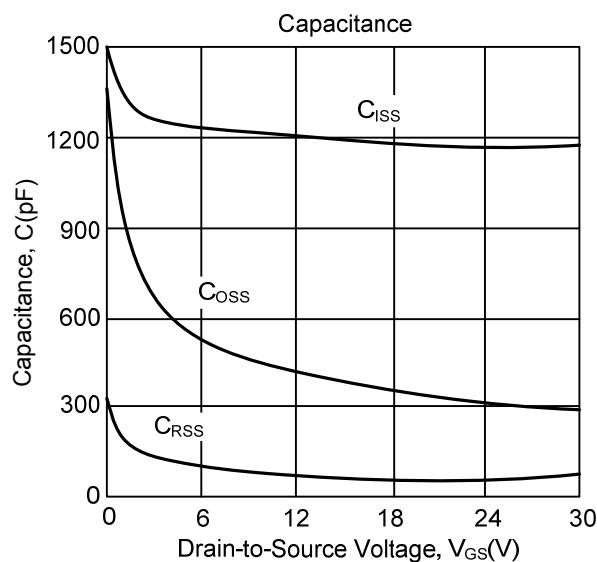
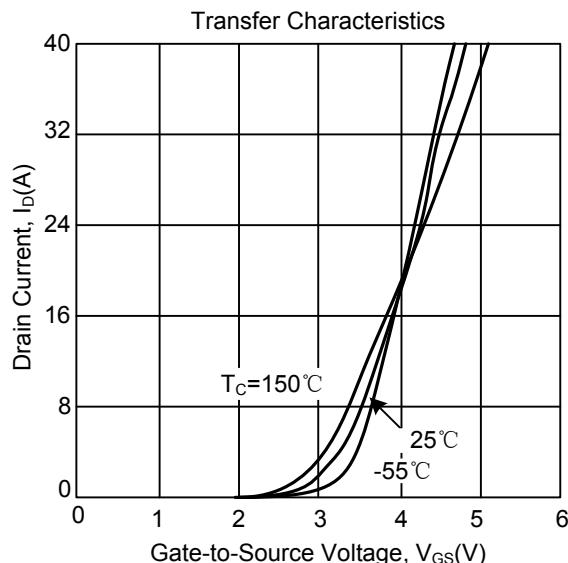
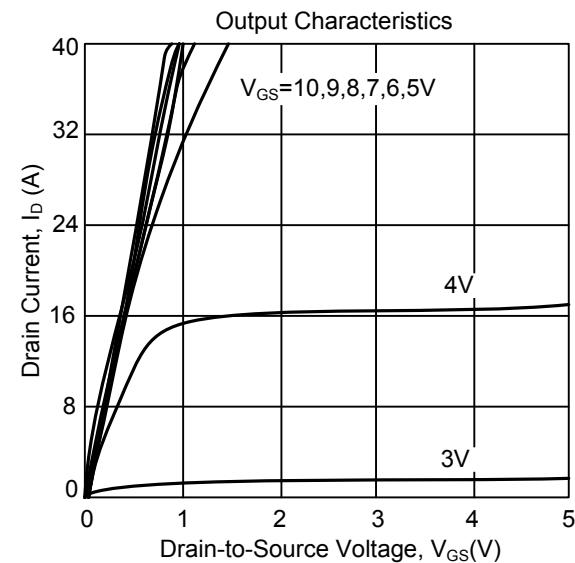
| PARAMETER  | SYMBOL              | TEST CONDITIONS   | MIN | TYP  | MAX       | UNIT             |
|--|---------------------|---|-----|------|-----------|------------------|
| <b>OFF CHARACTERISTICS</b>                             |                     |   |     |      |           |                  |
| Drain-Source Breakdown Voltage                         | $BV_{DSS}$          | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$   | 30  |      |           | V                |
| Drain-Source Leakage Current                           | $I_{DSS}$           | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$   |     |      | 1         | $\mu\text{A}$    |
| Gate-Source Leakage Current                            | $I_{GSS}$           | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$   |     |      | $\pm 100$ | nA               |
| <b>ON CHARACTERISTICS</b>                              |                     |   |     |      |           |                  |
| Gate Threshold Voltage                                 | $V_{GS(\text{TH})}$ | $V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$  | 1.0 |      |           | V                |
| Static Drain-Source On-State Resistance<br>(Note 2)    | $R_{DS(\text{ON})}$ | $V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$<br>$V_{GS} = 4.5 \text{ V}, I_D = 12.5 \text{ A}$                         |     | 20   | 30        | $\text{m}\Omega$ |
| <b>DYNAMIC CHARACTERISTICS</b>                         |                     |   |     |      |           |                  |
| Input Capacitance                                      | $C_{ISS}$           | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1\text{MHz}$  |     | 1170 |           | pF               |
| Output Capacitance                                     | $C_{OSS}$           |   |     | 320  |           | pF               |
| Reverse Transfer Capacitance                           | $C_{RSS}$           |   |     | 60   |           | pF               |
| <b>SWITCHING CHARACTERISTICS</b>                       |                     |   |     |      |           |                  |
| Turn-On Delay Time                                     | $t_{D(\text{ON})}$  | $V_{DD} = 15 \text{ V}, I_D = 30 \text{ A}, R_L = 0.5 \Omega, V_{GS} = 10 \text{ V}, R_G = 7.5 \Omega$<br>(Note 4, 5) |     | 10   | 20        | ns               |
| Turn-On Rise Time                                      | $t_R$               |   |     | 10   | 20        | ns               |
| Turn-Off Delay Time                                    | $t_{D(\text{OFF})}$ |   |     | 25   | 40        | ns               |
| Turn-Off Fall Time                                     | $t_F$               |   |     | 15   | 30        | ns               |
| Total Gate Charge                                      | $Q_G$               | $V_{DS} = 15 \text{ V}, I_D = 30 \text{ A}, V_{GS} = 10 \text{ V}$<br>(Note 4, 5)                                     |     | 18   | 35        | nC               |
| Gate-Source Charge                                     | $Q_{GS}$            |   |     | 5.5  |           | nC               |
| Gate-Drain Charge                                      | $Q_{GD}$            |   |     | 2    |           | nC               |
| <b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b> |                     |   |     |      |           |                  |
| Drain-Source Diode Forward Voltage                     | $V_{SD}$            | $V_{GS} = 0 \text{ V}, I_F = 30 \text{ A}$  |     | 1.1  | 1.5       | V                |
| Maximum Continuous Drain-Source Diode Forward Current  | $I_S$               |   |     |      | 30        | A                |
| Maximum Pulsed Drain-Source Diode Forward Current      | $I_{SM}$            |   |     |      | 40        | A                |
| Reverse Recovery Time                                  | $t_{RR}$            | $I_F = 30 \text{ A}, dI_F/dt = 100 \text{ A}/\mu\text{s}$   |     | 50   | 100       | ns               |

Notes: 1. Guaranteed by design, not subject to production testing.

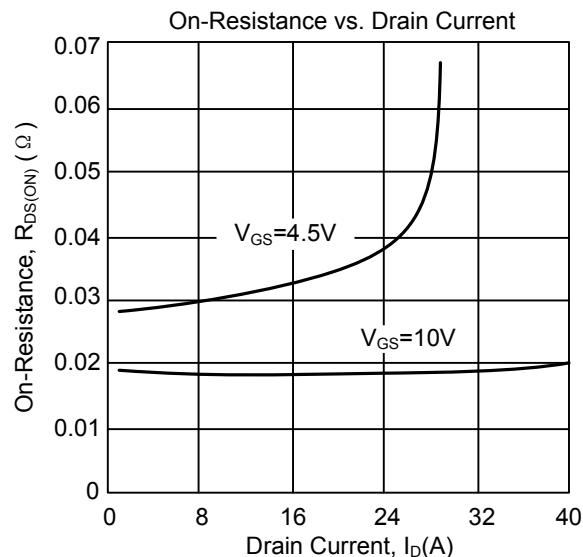
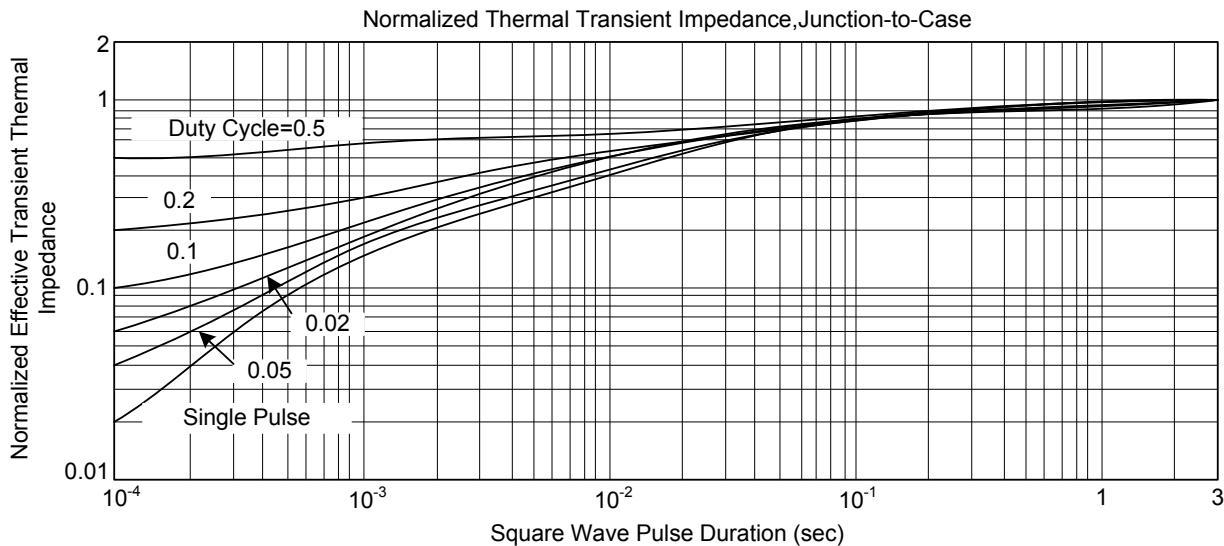
2. Pulse Test: Pulse width  $\leq 300 \mu\text{s}$ , Duty cycle  $\leq 2\%$

3. Essentially independent of operating temperature

■ TYPICAL CHARACTERISTICS



## ■ TYPICAL CHARACTERISTICS(Cont)



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